



#81/IDS  
Dixon  
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Complete if Known	
		Application Number	
		Filing Date	November 2, 2001
		First Named Inventor	Wilfred Lerch et al
		Group Art Unit	
		Examiner Name	
		Attorney Docket No.	AZ.2964

U. S. PATENT DOCUMENTS							
Examiner Initials	Cite No.	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date

FOREIGN PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation
							Yes No
WLR	2	WO 99/01895	14 Jan 1999	WIPO			X
WLR	5	WO 99/39381	05 Aug 1999	WIPO			X

OTHER PRIOR ART B NON PATENT LITERATURE DOCUMENTS		
Examiner Initials	Cite No.	
WLR	1	XP-002101565 "Rapid Thermal Process Requirements for the Annealing of Ultra-Shallow Junctions"
WLR	3	XP-000669354 "Simulation of Rapid Thermal Annealed Boron Ultra-Shallow Junctions in Inert and Oxidizing Ambient"
WLR	4	XP-000974859 "The Effects of Small Concentrations of Oxygen in RTP Annealing of Low Energy Boron, BF <sub>2</sub> and Arsenic Ion Implants"

Examiner	<i>James L. Maldonado</i>	Date	11/30/01
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